

TOSHIBA**MICROWAVE SEMICONDUCTOR**
TECHNICAL DATA**MICROWAVE POWER GaN HEMT**
TGI1314-50L**FEATURES****■ HIGH POWER**

Pout=47.0dBm at Pin=42.0dBm

■ HIGH GAIN

GL=8.0dB at 13.75GHz to 14.5GHz

■ BROAD BAND INTERNALLY MATCHED HEMT

HERMETICALLY SEALED PACKAGE

■ LOW INTERMODULATION DISTORTION

IM3(Min.)=-25dBc at Po=40.0dBm

Single Carrier Level

RF PERFORMANCE SPECIFICATIONS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Output Power	Pout	VDS = 24V IDSset \leq 2.0A f = 13.75 to 14.5GHz @ Pin=42dBm	dBm	46.0	47.0	—
Gain Flatness	ΔG		dB	—	—	± 0.8
Drain Current	IDS1		A	—	5.0	6.0
Power Added Efficiency	η_{add}		%	—	29	—
Gate Current	I_g_{RF}		mA	-40	—	+100
Linear Gain	GL	@Pin=20dBm	dB	7.0	8.0	—
3rd Order Intermodulation Distortion	IM3	Two-Tone Test Po= 40.0dBm (Single Carrier Level)	dBc	-25	—	—
Drain Current	IDS2		A	—	5.0	6.0
Channel Temperature Rise	ΔT_{ch}	(VDS X IDS + Pin - Pout) X Rth(c-c)	°C	—	130	150

Recommended gate resistance(Rg) : Rg= 13.3 Ω (TYP.)

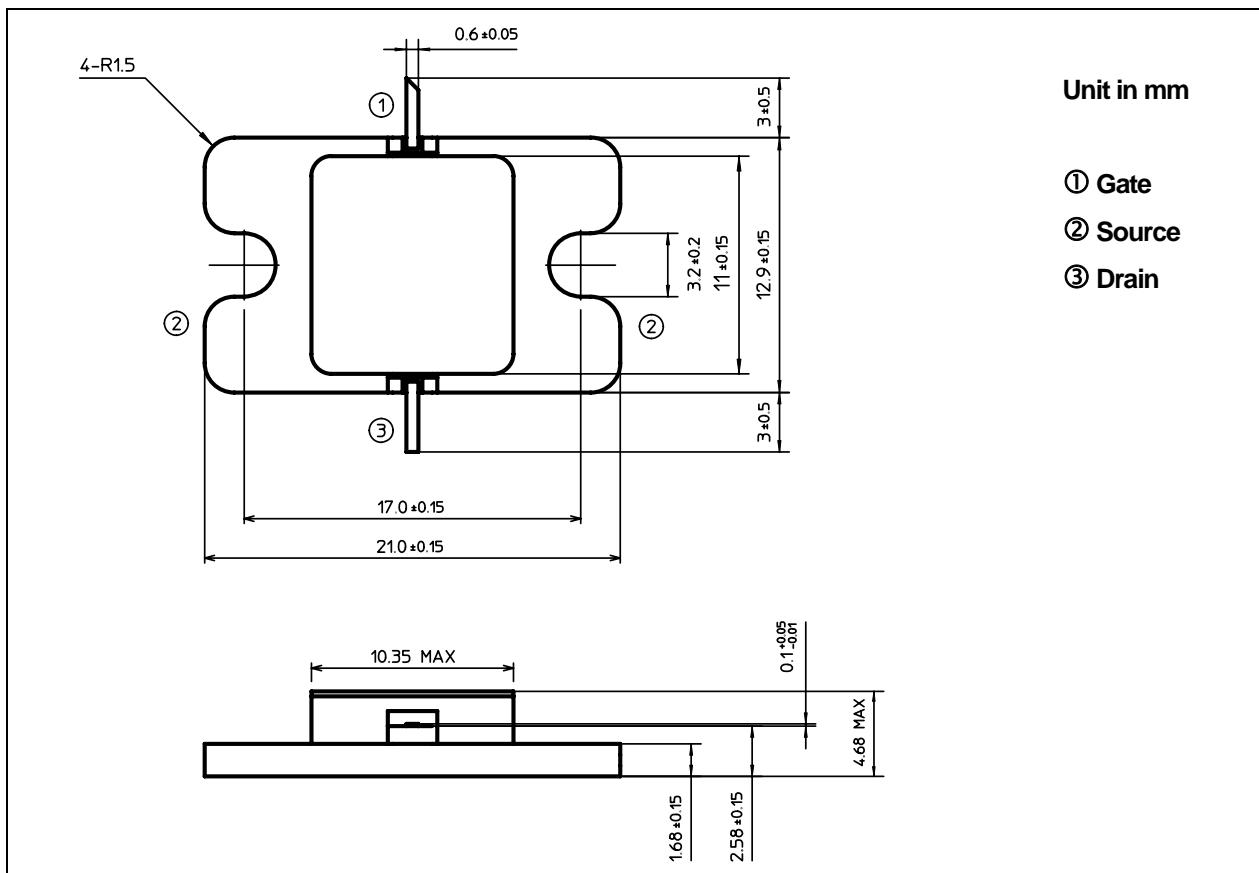
ELECTRICAL CHARACTERISTICS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	CONDITIONS	UNIT	MIN.	TYP.	MAX.
Transconductance	gm	VDS= 5V IDS= 5.0A	S	—	4.5	—
Pinch-off Voltage	VGSoff	VDS= 5V IDS= 23mA	V	-1	-4	-6
Saturated Drain Current	IDSS	VDS= 5V VGS= 0V	A	—	15	—
Gate-Source Breakdown Voltage	VGSO	IGS= -10mA	V	-10	—	—
Thermal Resistance	Rth(c-c)	Channel to Case	°C/W	—	—	1.6

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ABSOLUTE MAXIMUM RATINGS (Ta= 25°C)

CHARACTERISTICS	SYMBOL	UNIT	RATING
Drain-Source Voltage	V _{DS}	V	50
Gate-Source Voltage	V _{GS}	V	-10
Drain Current	I _{DS}	A	15
Total Power Dissipation (T _c = 25 °C)	P _T	W	140
Channel Temperature	T _{ch}	°C	250
Storage	T _{stg}	°C	-65 to +175

PACKAGE OUTLINE (7- AA07A)**HANDLING PRECAUTIONS FOR PACKAGE MODEL**

Soldering iron should be grounded and the operating time should not exceed 10 seconds at 260°C.